LSD55R380HT-VB Datasheet

N-Channel 550V (D-S) Power MOSFET

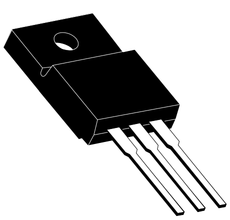
PRODUCT SUMMARY		
V_{DS} (V)	550	
$R_{DS(on)}$ at 25 °C (Ω)	V_{GS} = 10 V	0.26
Q_g max. (nC)	150	
Q_{gs} (nC)	12	
Q_{gd} (nC)	25	
Configuration	Single	

FEATURES

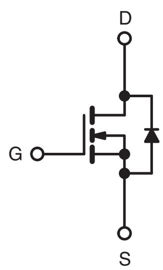
- Optimal Design
  - Low Area Specific On-Resistance
  - Low Input Capacitance (C_{iss})
  - Reduced Capacitive Switching Losses
  - High Body Diode Ruggedness
  - Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
  - Low Cost
  - Simple Gate Drive Circuitry
  - Low Figure-of-Merit (FOM): R_{on} x Q_g
  - Fast Switching

RoHS* COMPLIANT
HALOGEN FREE Available

TO-220 FULLPAK



Top View



N-Channel MOSFET

APPLICATIONS

- Consumer Electronics
  - Displays (LCD or Plasma TV)
- Server and Telecom Power Supplies
  - SMPS
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
- Battery Chargers
- SMPS
  - Power Factor Correction (PFC)

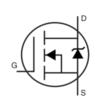
ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	550	V
Gate-Source Voltage			V_{GS}	± 20	
Gate-Source Voltage AC (f > 1 Hz)				30	
Continuous Drain Current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	18	A
		T_C = 100 °C		11	
Pulsed Drain Current[a]			I_{DM}	56	
Linear Derating Factor				2.2	W/°C
Single Pulse Avalanche Energy[b]			E_{AS}	281	mJ
Maximum Power Dissipation			P_D	60	W
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Drain-Source Voltage Slope	T_J = 125 °C		dV/dt	24	V/ns
Reverse Diode dV/dt[d]				0.36	
Soldering Recommendations (Peak Temperature)	for 10 s			300[c]	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature.
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 10 mH, R_g = 25 Ω, I_{AS} = 7.5 A.
c. 1.6 mm from case.
d. $I_{SD} \leq I_D$, starting T_J = 25 °C.

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	550	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 250 μA	-	0.56	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2	-	4	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 400 V, V_{GS} = 0 V, T_J = 125 °C	-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 10 A	-	0.26	-	Ω
Forward Transconductance	g_{fs}	V_{DS} = 50 V, I_D = 10 A	-	12	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	3094	-	pF
Output Capacitance	C_{oss}		-	152	-	
Reverse Transfer Capacitance	C_{rss}		-	13	-	
Effective output capacitance, energy related[a]	$C_{o(er)}$	V_{GS} = 0 V, V_{DS} = 0 V to 400 V	-	131	-	
Effective output capacitance, time related[b]	$C_{o(tr)}$		-	189	-	
Total Gate Charge	Q_g	V_{GS} = 10 V, I_D = 10 A, V_{DS} = 400 V	-	80	150	nC
Gate-Source Charge	Q_{gs}		-	12	-	
Gate-Drain Charge	Q_{gd}		-	25	-	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 400 V, I_D = 10 A, V_{GS} = 10 V, R_g = 9.1 Ω	-	24	50	ns
Rise Time	t_r		-	31	62	
Turn-Off Delay Time	$t_{d(off)}$		-	117	176	
Fall Time	t_f		-	56	112	
Gate Input Resistance	R_g	f = 1 MHz, open drain	-	1.8	-	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	20	A
Pulsed Diode Forward Current	I_{SM}		-	-	80	
Diode Forward Voltage	V_{SD}	T_J = 25 °C, I_S = 10 A, V_{GS} = 0 V	-	-	1.2	V
Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = I_S = 10 A, dI/dt = 100 A/μs, V_R = 20 V	-	437	-	ns
Reverse Recovery Charge	Q_{rr}		-	5.9	-	μC
Reverse Recovery Current	I_{RRM}		-	25	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}.

b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

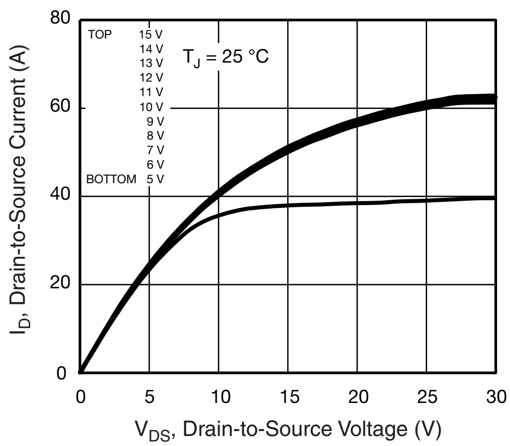


Fig. 1 - Typical Output Characteristics

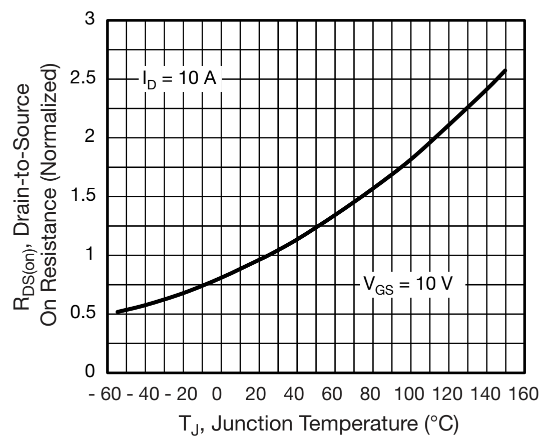


Fig. 4 - Normalized On-Resistance vs. Temperature

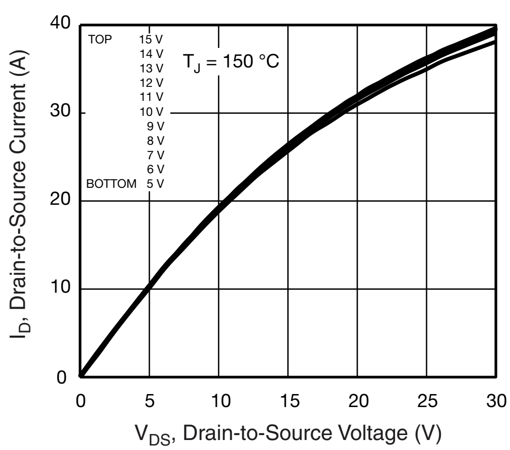


Fig. 2 - Typical Output Characteristics

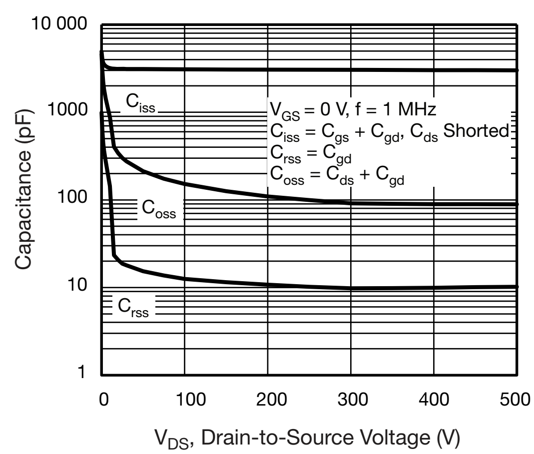


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

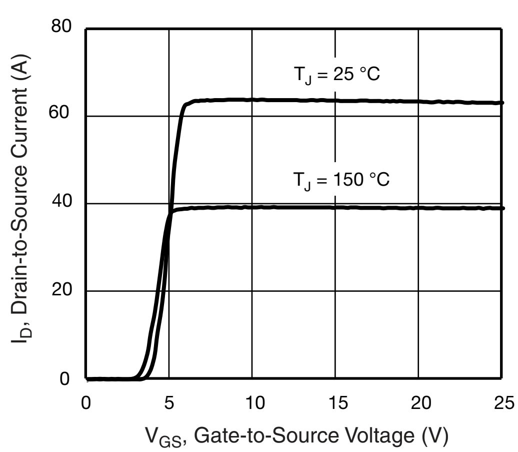


Fig. 3 - Typical Transfer Characteristics

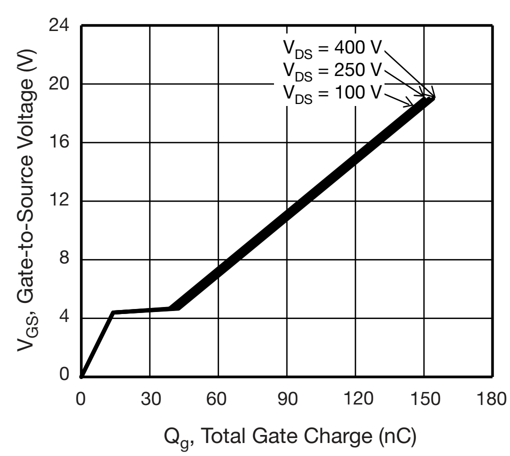


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

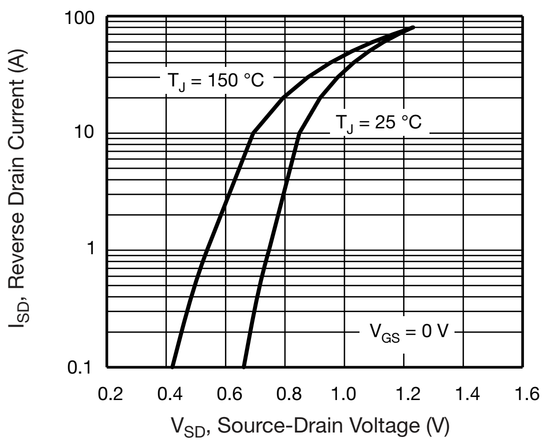


Fig. 7 - Typical Source-Drain Diode Forward Voltage

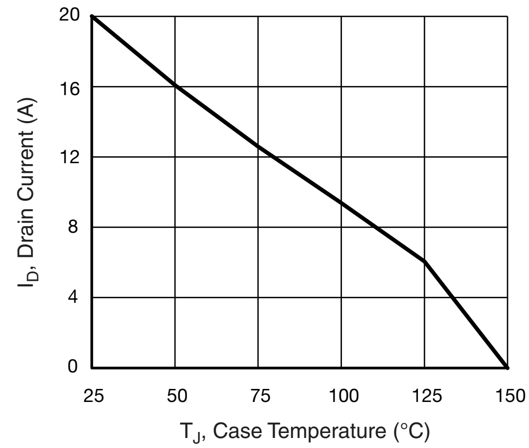


Fig. 9 - Maximum Drain Current vs. Case Temperature

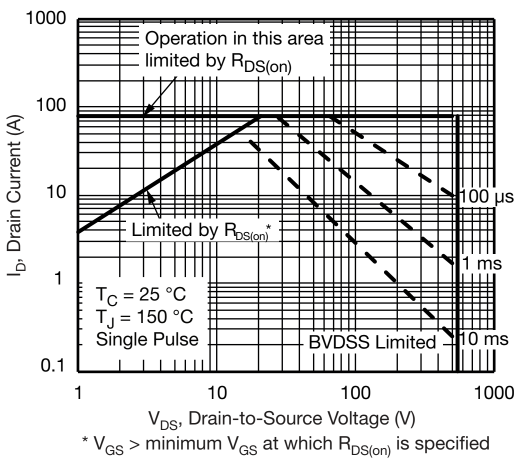


Fig. 8 - Maximum Safe Operating Area

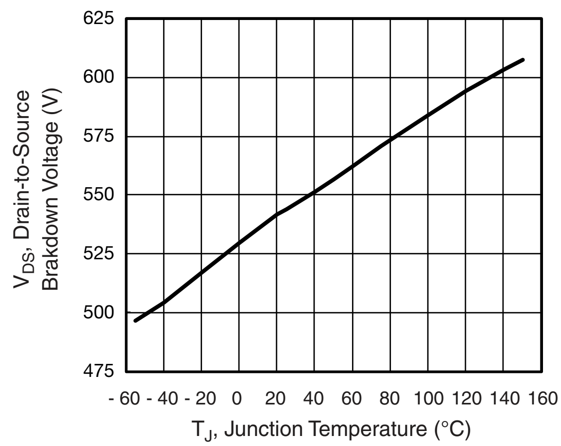


Fig. 10 - Temperature vs. Drain-to-Source Voltage

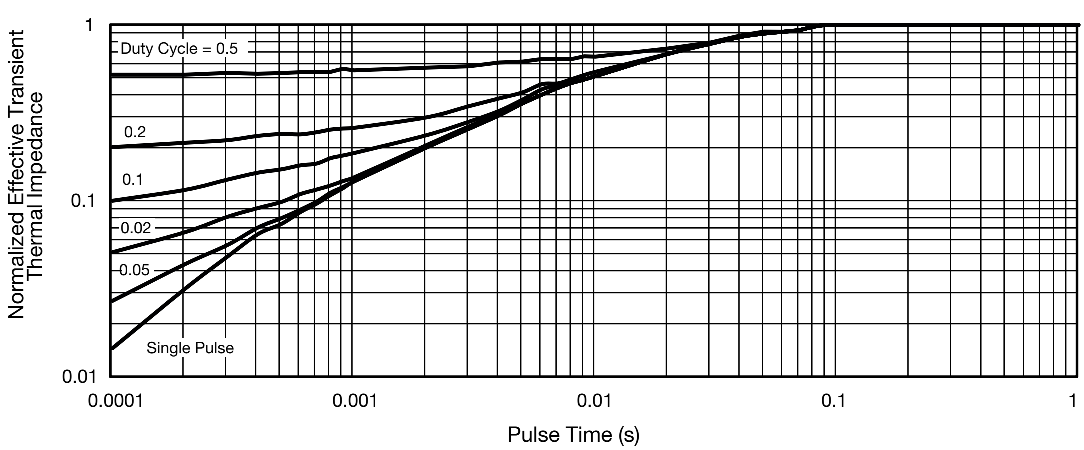


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

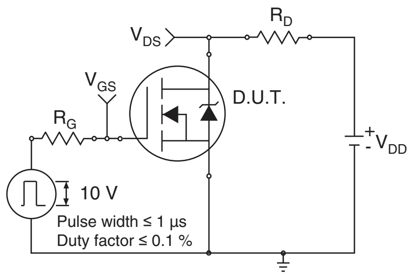


Fig. 12 - Switching Time Test Circuit

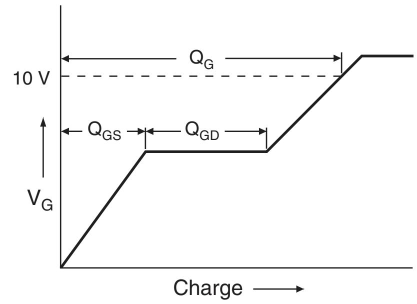


Fig. 16 - Basic Gate Charge Waveform

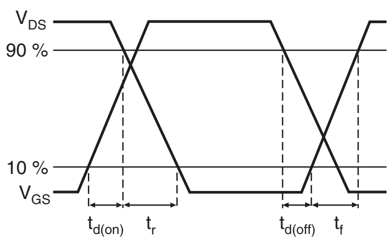


Fig. 13 - Switching Time Waveforms

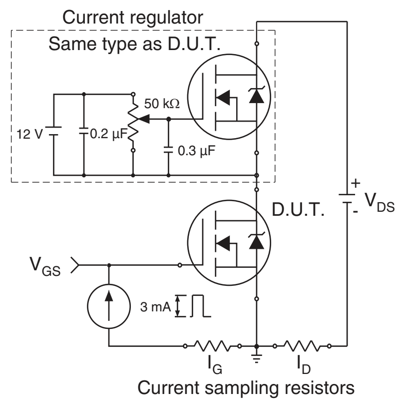


Fig. 17 - Gate Charge Test Circuit

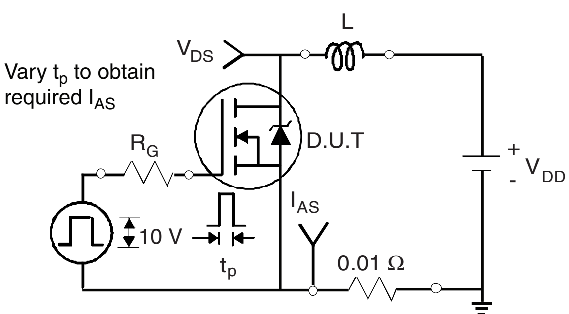


Fig. 14 - Unclamped Inductive Test Circuit

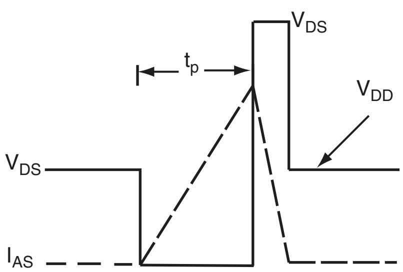
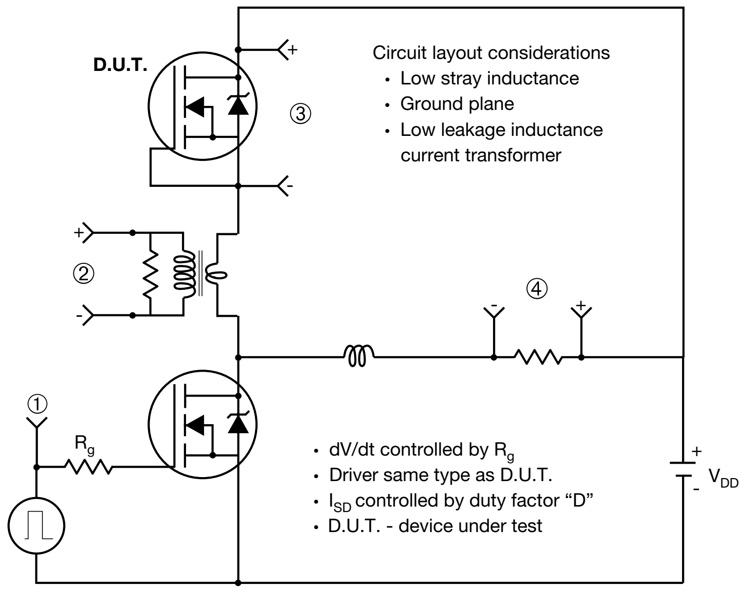
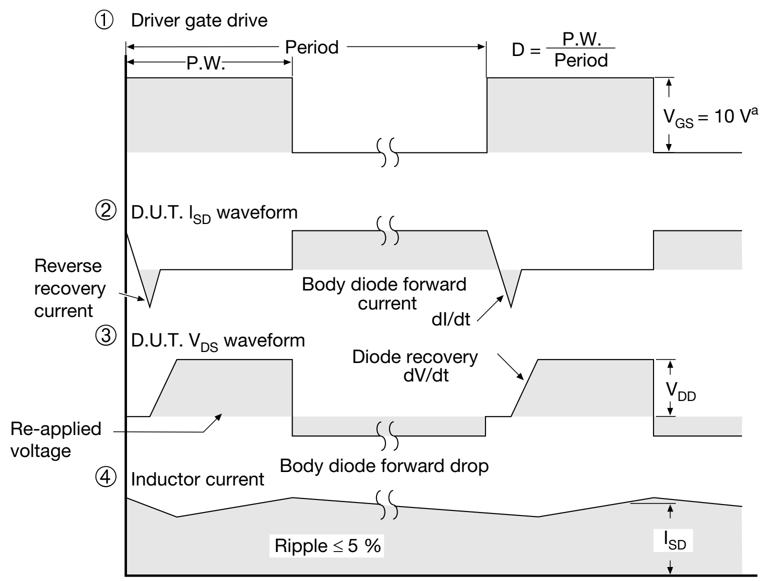


Fig. 15 - Unclamped Inductive Waveforms

Peak Diode Recovery dV/dt Test Circuit



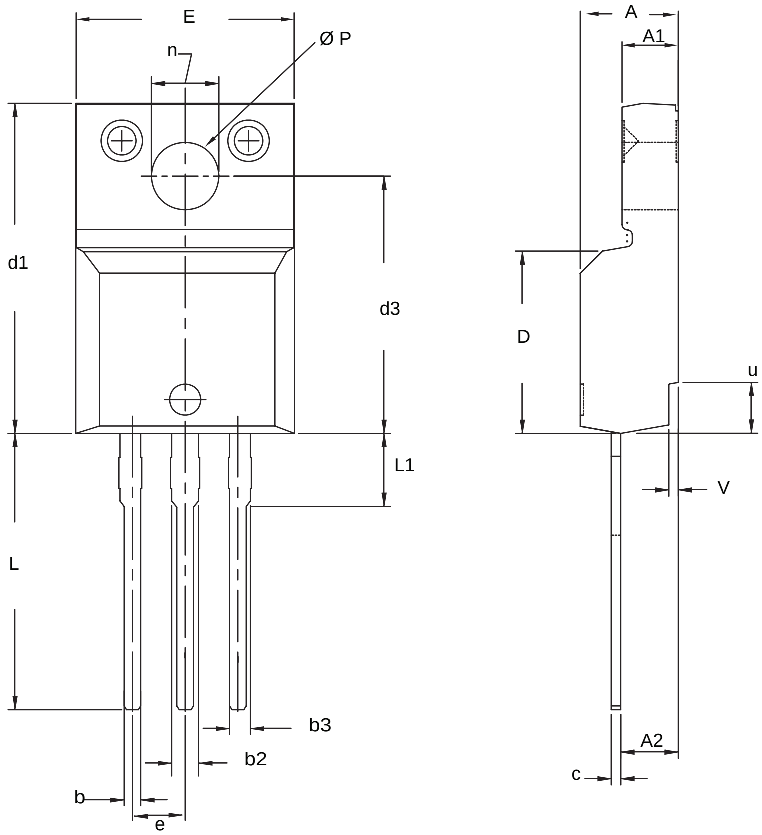


Note

a. V_{GS} = 5 V for logic level devices

Fig. 18 - For N-Channel

TO-220 FULLPAK (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
v	0.400	0.500	0.016	0.020
ECN: X09-0126-Rev. B, 26-Oct-09 DWG: 5972				

Notes

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet C_{pk} > 1.33.
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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